

2SA1487

Silicon PNP epitaxial planer type

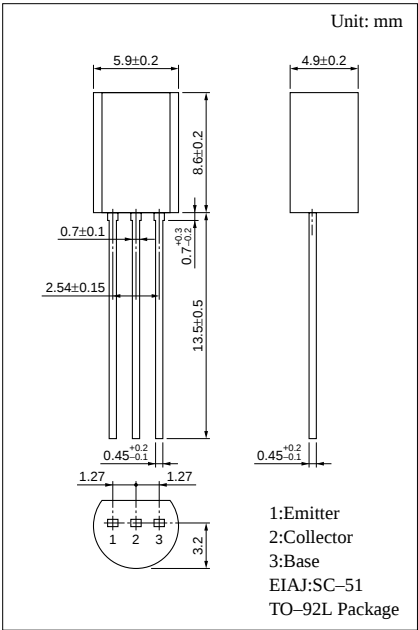
For video amplifier

Features

- High transition frequency f_T .
- Small collector output capacitance C_{ob} .

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	-85	V
Collector to emitter voltage	V_{CEO}	-85	V
Emitter to base voltage	V_{EBO}	-4	V
Peak collector current	I_{CP}	-100	mA
Collector current	I_C	-50	mA
Collector power dissipation	P_C	1	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 ~ +150	°C



Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CEO}	$V_{CE} = -60V, I_B = 0$			-10	μA
Collector to base voltage	V_{CBO}	$I_C = -100\mu A, I_E = 0$	-85			V
Collector to emitter voltage	V_{CEO}	$I_C = 1mA, I_B = 0$	-85			V
Emitter to base voltage	V_{EBO}	$I_E = -100\mu A, I_C = 0$	-4			V
Forward current transfer ratio	h_{FE}	$V_{CE} = -5V, I_C = -10mA$	60			
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10mA, I_B = -1mA$			-0.5	V
Transition frequency	f_T	$V_{CB} = -5V, I_E = 10mA, f = 200MHz$		500		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		2.7		pF

